

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-20V	90mΩ @ V _{GS} = -4.5V	-3.1A
	250mΩ @ V _{GS} = -2.5V	-1.8A

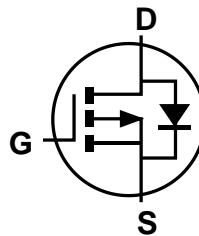
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

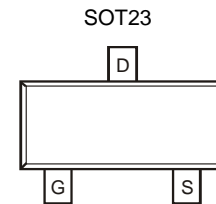
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors



Top View



Internal Schematic



Top View

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

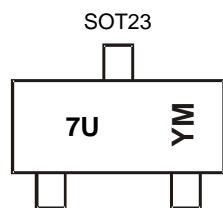
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2170U-7	SOT23	3,000/Tape & Reel
DMP2170U-13	SOT23	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



7U = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: D = 2016)
 M = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023
Code	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	-20	V	
Gate-Source Voltage	V_{GSS}	± 12	V	
Continuous Drain Current (Note 6) $V_{GS} = -4.5\text{V}$	I_D	Steady State $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	-3.1 -2.5	A
Maximum Continuous Body Diode Forward Current (Note 6)		I_S	-1.25	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)	I_{DM}	-13	A	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.78	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State $R_{\theta JA}$	163	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	P_D	1.28	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State $R_{\theta JA}$	99	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	-	-	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	-	-	-1.0	μA	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.4	-1.01	-1.25	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	62 92 101	90 180 250	m Ω	$V_{GS} = -4.5\text{V}, I_D = -3.5\text{A}$ $V_{GS} = -2.7\text{V}, I_D = -3.0\text{A}$ $V_{GS} = -2.5\text{V}, I_D = -2.6\text{A}$
Diode Forward Voltage	V_{SD}	-	-0.8	-1.1	V	$V_{GS} = 0\text{V}, I_S = -1\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{ISS}	-	303	-	pF	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{OSS}	-	46	-	pF	
Reverse Transfer Capacitance	C_{RSS}	-	37	-	pF	
Gate Resistance	R_g	-	16	-	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = -4.5\text{V}$)	Q_g	-	3.6	-	nC	$V_{DS} = -10\text{V}, I_D = -1.5\text{A}$
Total Gate Charge ($V_{GS} = -10\text{V}$)	Q_g	-	7.8	-	nC	
Gate-Source Charge	Q_{GS}	-	0.6	-	nC	
Gate-Drain Charge	Q_{gd}	-	1.1	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	5.4	-	ns	$V_{DD} = -10\text{V}, V_{GS} = -4.5\text{V}, I_D = -3.5\text{A}, R_G = 6\Omega$
Turn-On Rise Time	t_R	-	18.3	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	16.2	-	ns	
Turn-Off Fall Time	t_F	-	13.6	-	ns	
Body Diode Reverse Recovery Time	t_{RR}	-	5.5	-	ns	$I_S = -2.0\text{A}, di/dt = -100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	-	1.23	-	nC	$I_S = -2.0\text{A}, di/dt = -100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

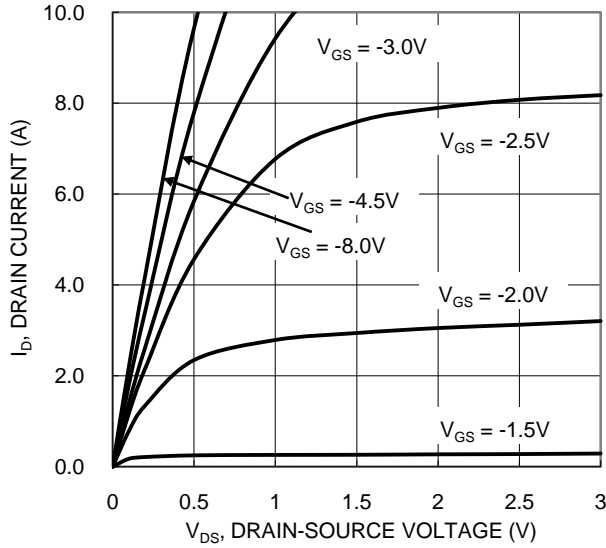


Figure 1. Typical Output Characteristic

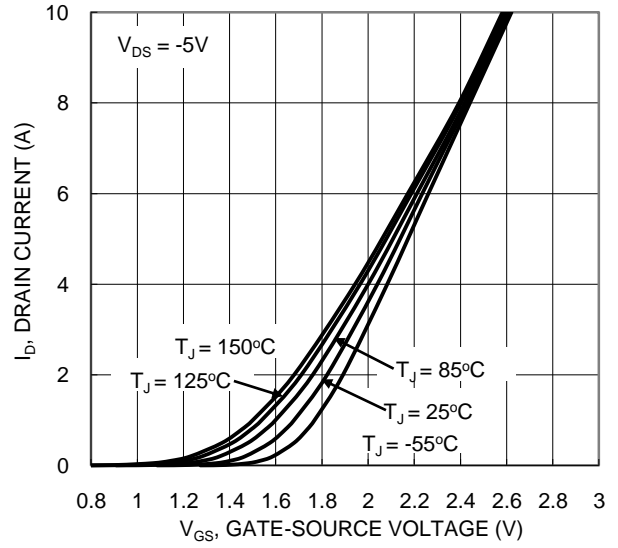


Figure 2. Typical Transfer Characteristic

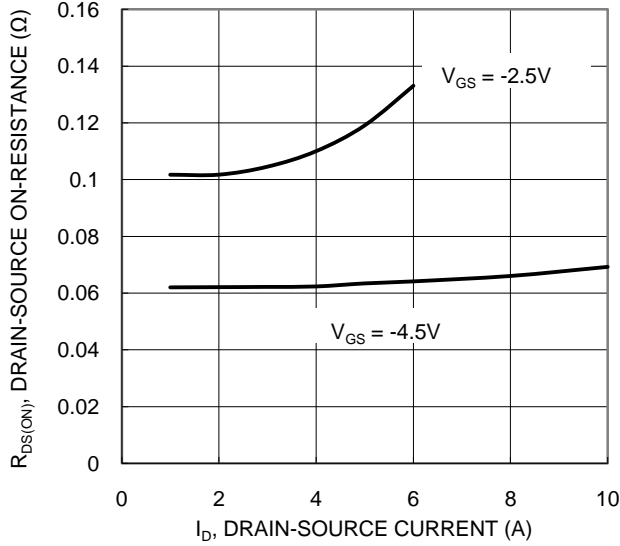


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

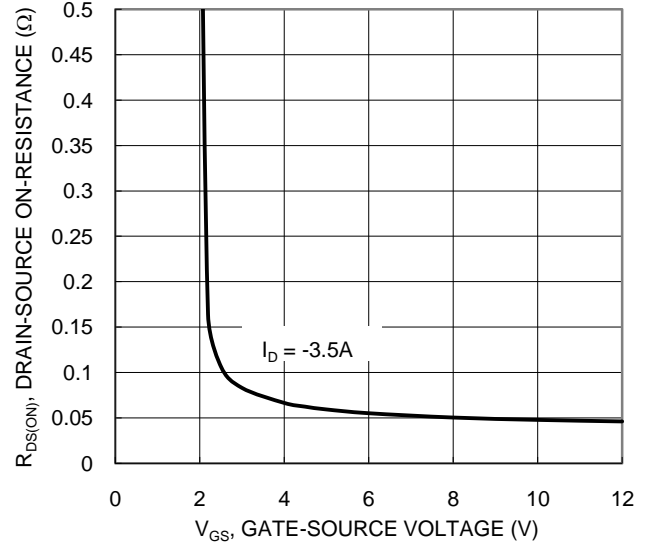


Figure 4. Typical Transfer Characteristic

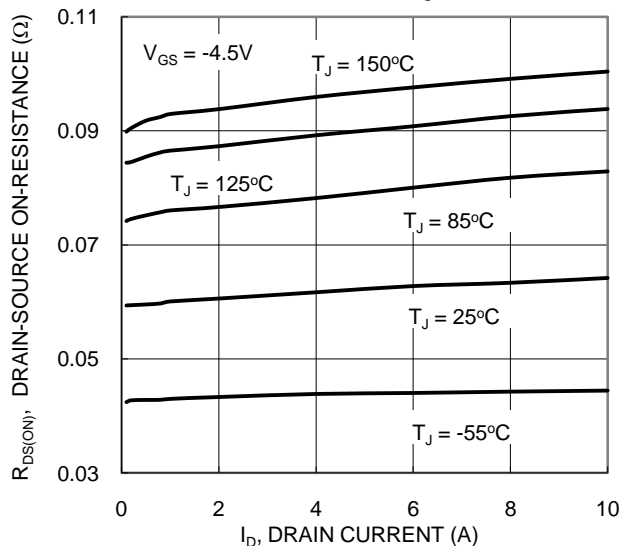


Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature

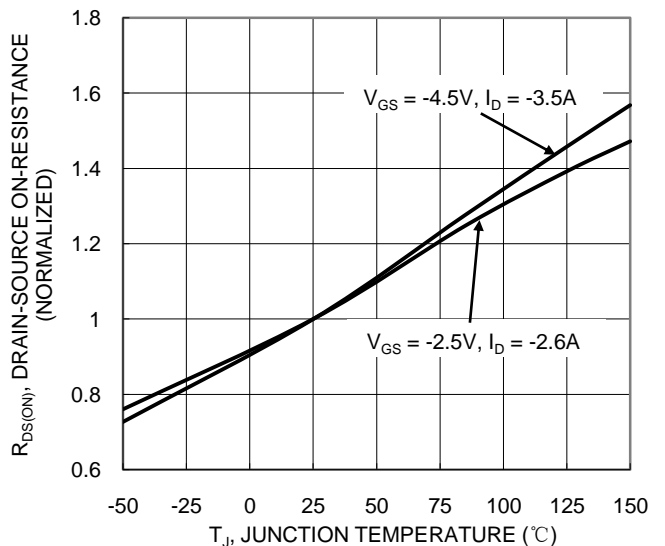
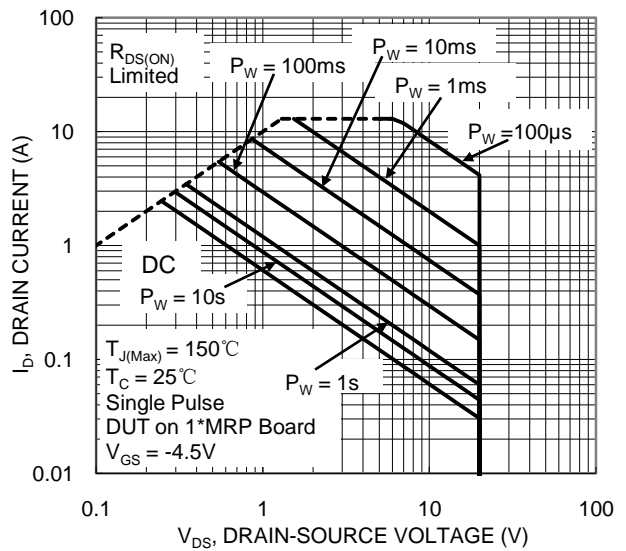
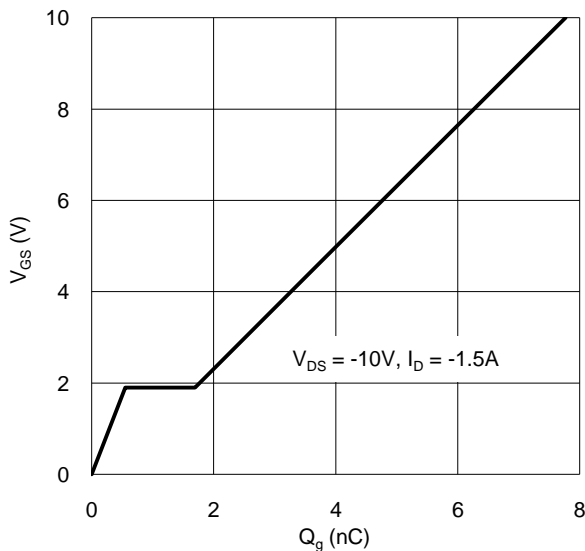
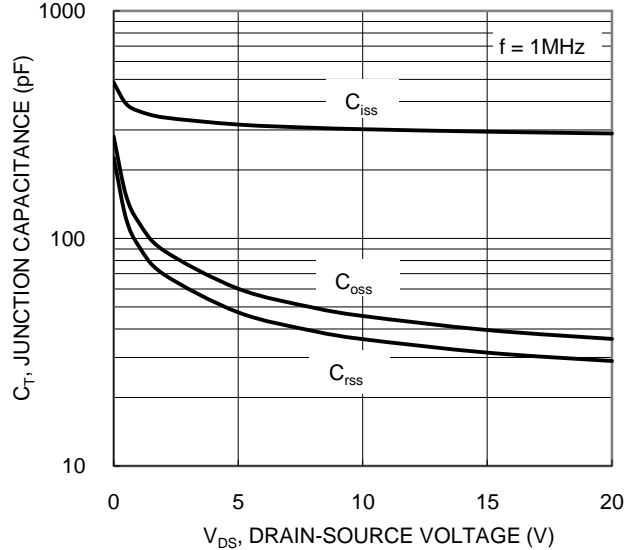
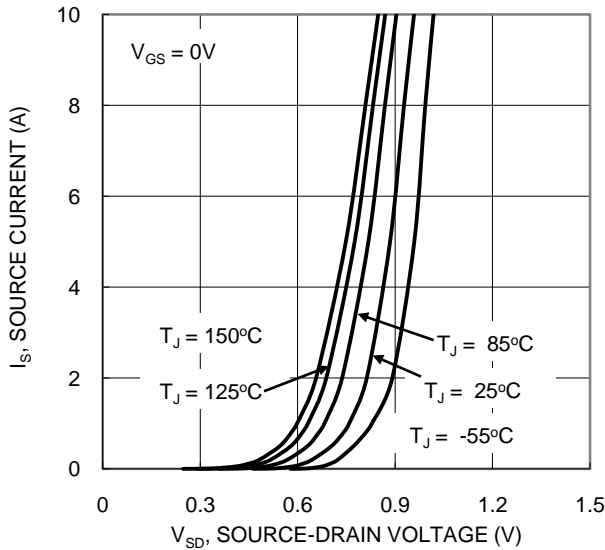
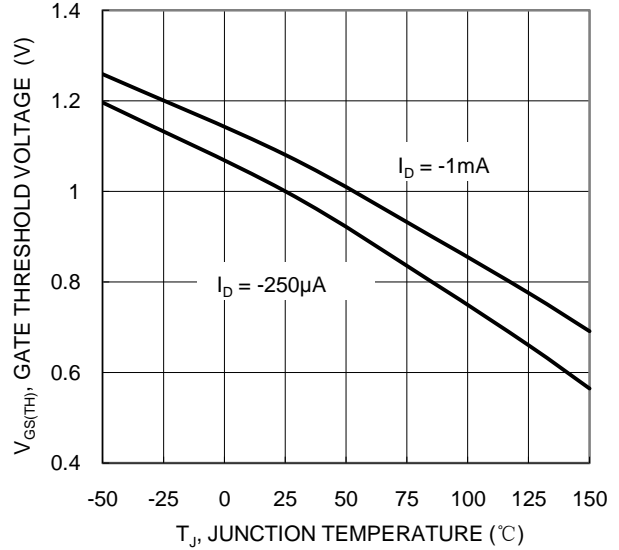
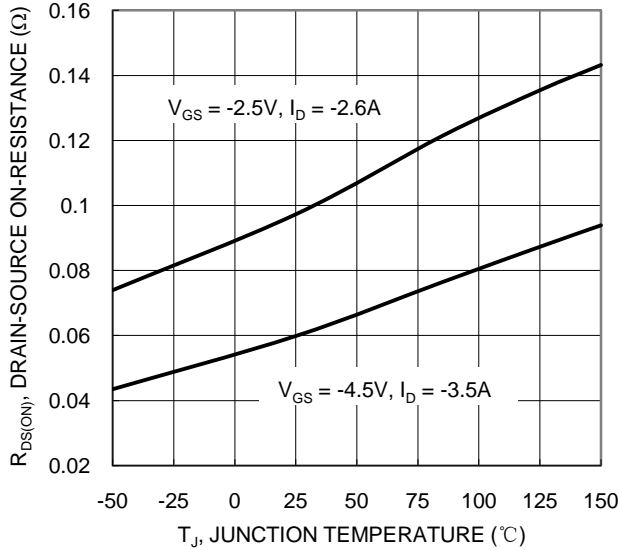


Figure 6. On-Resistance Variation with Junction Temperature



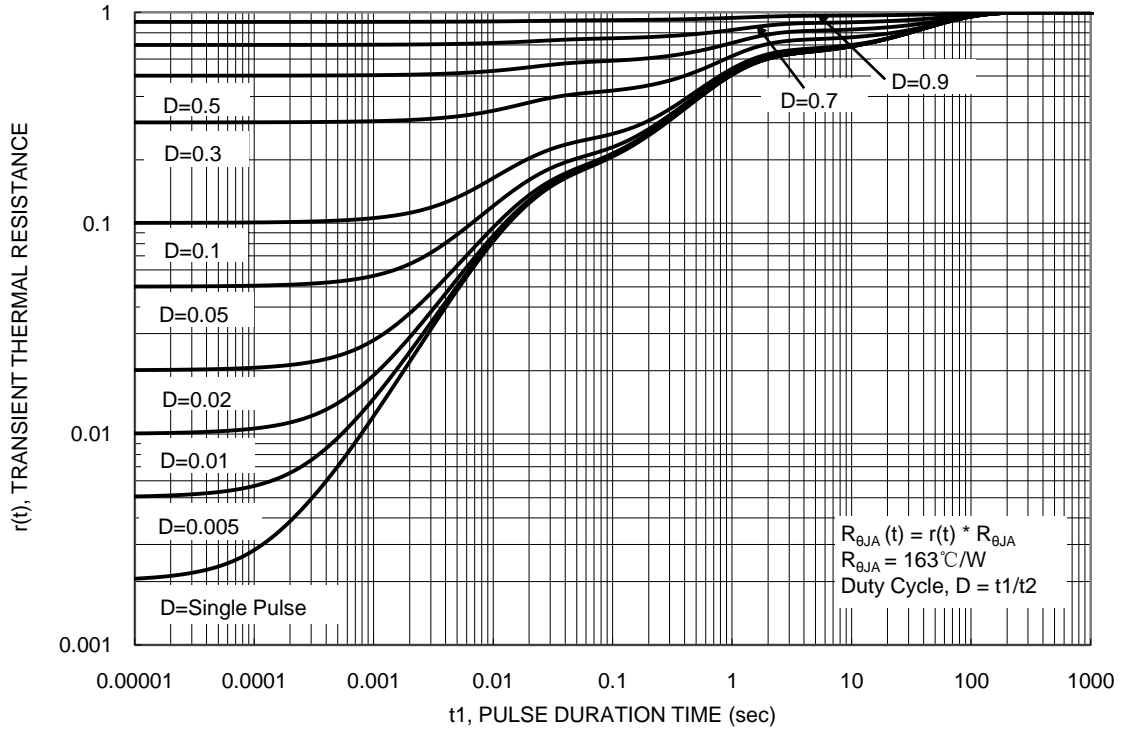
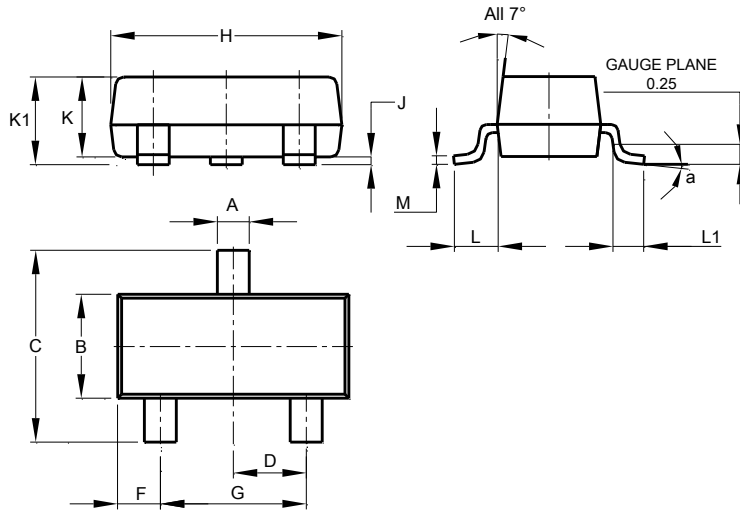


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

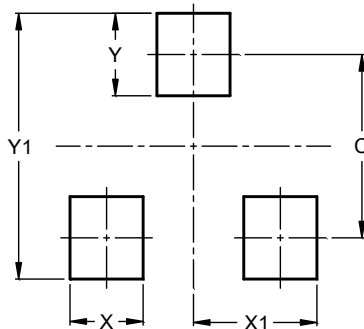


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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